

**PowerMOS transistor
Isolated version of BUK454-200A/B**
BUK474-200A/B**GENERAL DESCRIPTION**

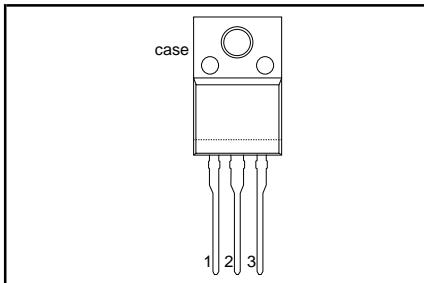
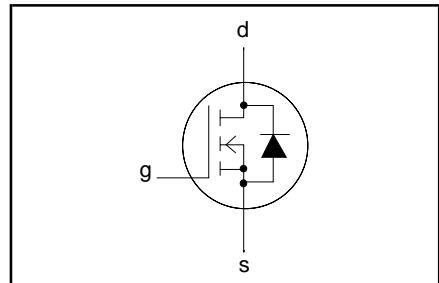
N-channel enhancement mode field-effect power transistor in a plastic full-pack envelope. The device is intended for use in Switched Mode Power Supplies (SMPS), motor control, welding, DC/DC and AC/DC converters, and in general purpose switching applications.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	UNIT
	BUK474			
V _{DS}	Drain-source voltage	-200A	-200B	V
I _D	Drain current (DC)	200	200	A
P _{tot}	Total power dissipation	5.3	4.7	W
R _{DS(ON)}	Drain-source on-state resistance	25	25	Ω
		0.4	0.5	

PINNING - SOT186A

PIN	DESCRIPTION
1	gate
2	drain
3	source
case	isolated

PIN CONFIGURATION**SYMBOL****LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
			-	-	-	-	
V _{DS}	Drain-source voltage	R _{GS} = 20 kΩ	-	-	200	200	V
	Drain-gate voltage		-	-	200	30	
	Gate-source voltage		-	-	-	-	
I _D	Drain current (DC)	T _{hs} = 25 °C	-	-	5.3	4.7	A
	Drain current (DC)		-	-	3.3	3.0	
	Drain current (pulse peak value)		-	-	21	19	
P _{tot}	Total power dissipation	T _{hs} = 25 °C	-	-	25	25	W
	Storage temperature		-	-	150	150	
	Junction temperature		-	-	150	150	

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-hs}	Thermal resistance junction to heatsink	with heatsink compound	-	-	5	K/W
R _{th j-a}	Thermal resistance junction to ambient		-	55	-	K/W

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STATIC CHARACTERISTICS $T_{hs} = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.25 \text{ mA}$	200	-	-	V
$V_{GS(TO)}$	Gate threshold voltage	$V_{DS} = V_{GS}; I_D = 1 \text{ mA}$	2.1	3.0	4.0	V
I_{DSS}	Zero gate voltage drain current	$V_{DS} = 200 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25^\circ\text{C}$	-	1	10	μA
I_{GSS}	Zero gate voltage drain current	$V_{DS} = 200 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125^\circ\text{C}$	-	0.1	1.0	mA
$R_{DS(ON)}$	Gate source leakage current	$V_{GS} = \pm 30 \text{ V}; V_{DS} = 0 \text{ V}$	-	10	100	nA
	Drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 3.5 \text{ A}$	BUK474-200A	0.35	0.4	Ω
			BUK474-200B	0.4	0.5	Ω

DYNAMIC CHARACTERISTICS $T_{hs} = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
g_{fs}	Forward transconductance	$V_{DS} = 25 \text{ V}; I_D = 3.5 \text{ A}$	3.5	5.0	-	S
C_{iss}	Input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz}$	-	700	850	pF
C_{oss}	Output capacitance		-	100	160	pF
C_{rss}	Feedback capacitance		-	50	80	pF
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 30 \text{ V}; I_D = 2.9 \text{ A}; V_{GS} = 10 \text{ V}; R_{GS} = 50 \Omega; R_{gen} = 50 \Omega$	-	12	20	ns
t_r	Turn-on rise time		-	45	70	ns
$t_{d(off)}$	Turn-off delay time		-	80	120	ns
t_f	Turn-off fall time		-	40	60	ns
L_d	Internal drain inductance	Measured from drain lead 6 mm from package to centre of die	-	4.5	-	nH
L_s	Internal source inductance	Measured from source lead 6 mm from package to source bond pad	-	7.5	-	nH

ISOLATION LIMITING VALUE & CHARACTERISTIC $T_{hs} = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{isol}	R.M.S. isolation voltage from all three terminals to external heatsink	$f = 50-60 \text{ Hz}; \text{sinusoidal waveform}; R.H. \leq 65\%; \text{clean and dustfree}$	-		2500	V
C_{isol}	Capacitance from T2 to external heatsink	$f = 1 \text{ MHz}$	-	10	-	pF

REVERSE DIODE LIMITING VALUES AND CHARACTERISTICS $T_{hs} = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{DR}	Continuous reverse drain current	-	-	-	5.3	A
I_{DRM}	Pulsed reverse drain current	-	-	-	21	A
V_{SD}	Diode forward voltage	$I_F = 5.3 \text{ A}; V_{GS} = 0 \text{ V}$	-	1.1	1.3	V
t_{rr}	Reverse recovery time	$I_F = 5.3 \text{ A}; -dI_F/dt = 100 \text{ A}/\mu\text{s}$	-	150	-	ns
Q_{rr}	Reverse recovery charge	$V_{GS} = 0 \text{ V}; V_R = 30 \text{ V}$	-	0.9	-	μC

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AVALANCHE LIMITING VALUE $T_{hs} = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
W_{DSS}	Drain-source non-repetitive unclamped inductive turn-off energy	$I_D = 9 \text{ A}$; $V_{DD} \leq 100 \text{ V}$; $V_{GS} = 10 \text{ V}$; $R_{GS} = 50 \Omega$	-	-	50	mJ

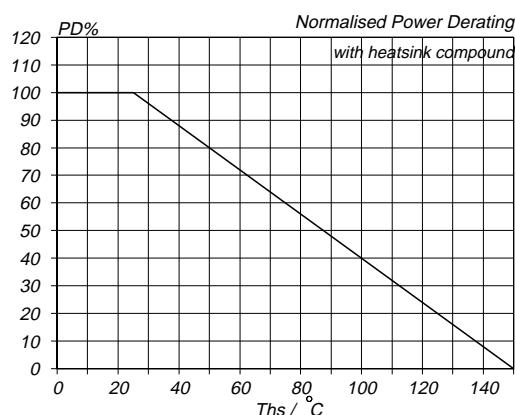


Fig. 1. Normalised power dissipation.
 $PD\% = 100 \cdot P_D / P_{D, 25^\circ\text{C}} = f(T_{hs})$

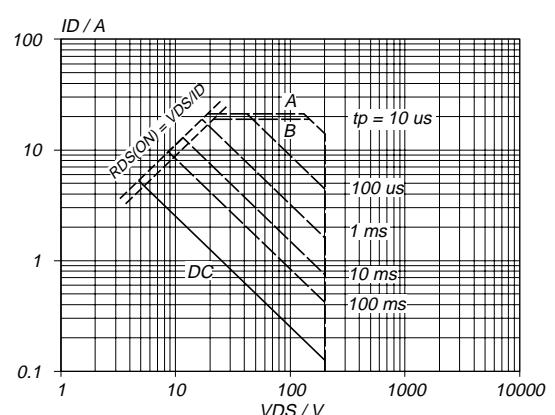


Fig. 3. Safe operating area. $T_{hs} = 25^\circ\text{C}$
 I_D & $I_{DM} = f(V_{DS})$; I_{DM} single pulse; parameter t_p

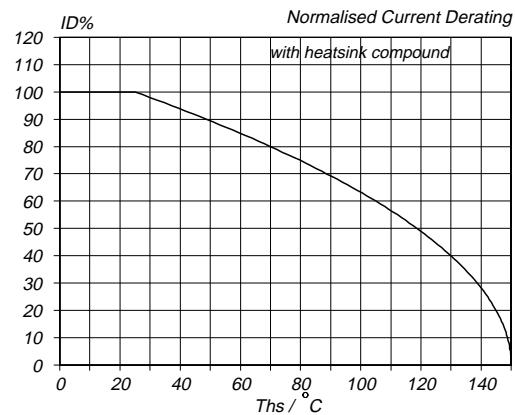


Fig. 2. Normalised continuous drain current.
 $ID\% = 100 \cdot I_D / I_{D, 25^\circ\text{C}} = f(T_{hs})$; conditions: $V_{GS} \geq 10 \text{ V}$

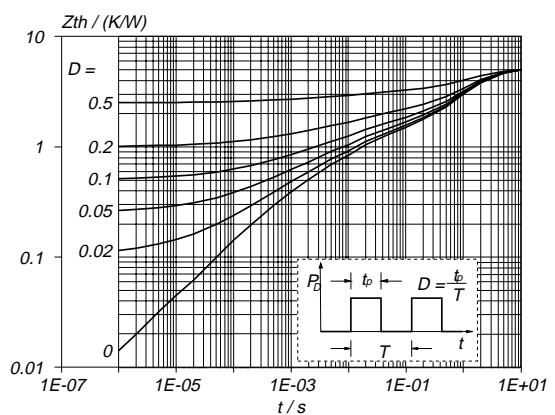


Fig. 4. Transient thermal impedance.
 $Z_{th, hs} = f(t)$; parameter $D = t_p/T$

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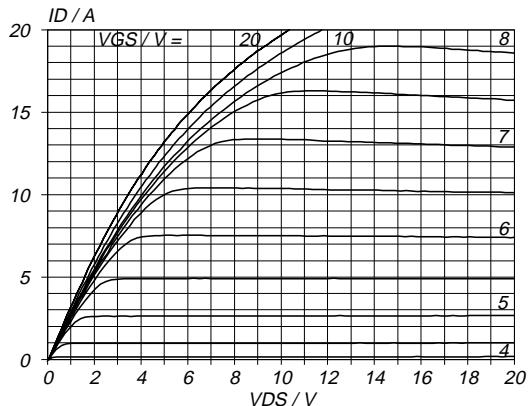


Fig.5. Typical output characteristics, $T_j = 25^\circ\text{C}$.
 $I_D = f(V_{DS})$; parameter V_{GS}

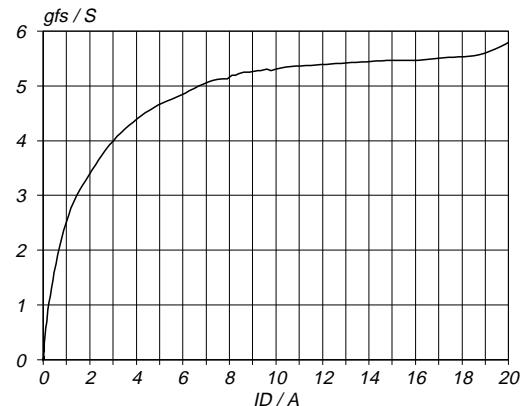


Fig.8. Typical transconductance, $T_j = 25^\circ\text{C}$.
 $g_{fs} = f(I_D)$; conditions: $V_{DS} = 25\text{ V}$

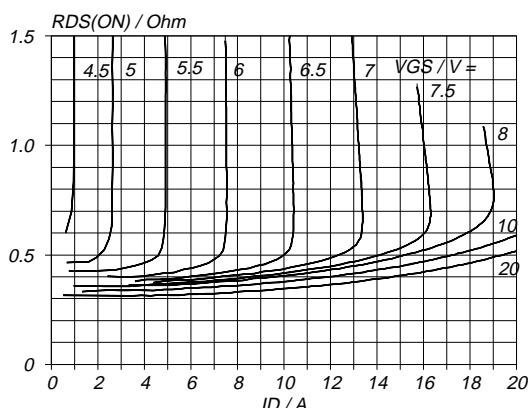


Fig.6. Typical on-state resistance, $T_j = 25^\circ\text{C}$.
 $R_{DS(ON)} = f(I_D)$; parameter V_{GS}

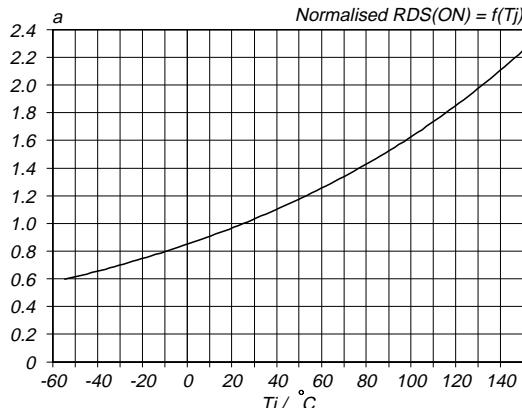


Fig.9. Normalised drain-source on-state resistance.
 $a = R_{DS(ON)}/R_{DS(ON)25^\circ\text{C}} = f(T_j)$; $I_D = 3.5\text{ A}$; $V_{GS} = 10\text{ V}$

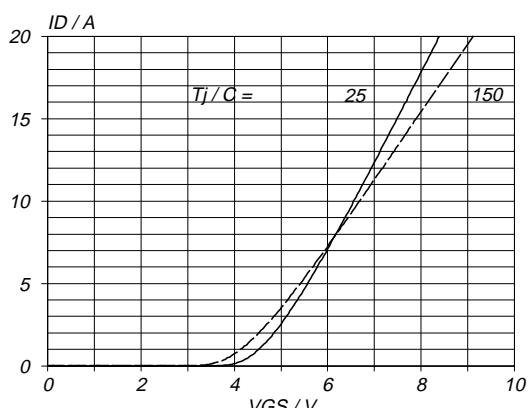


Fig.7. Typical transfer characteristics.
 $I_D = f(V_{GS})$; conditions: $V_{DS} = 25\text{ V}$; parameter T_j

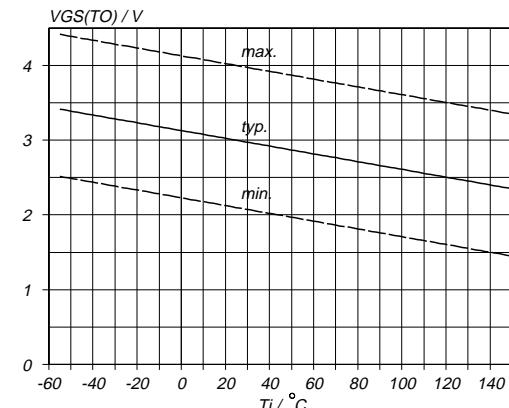


Fig.10. Gate threshold voltage.
 $V_{GS(TO)} = f(T_j)$; conditions: $I_D = 1\text{ mA}$; $V_{DS} = V_{GS}$

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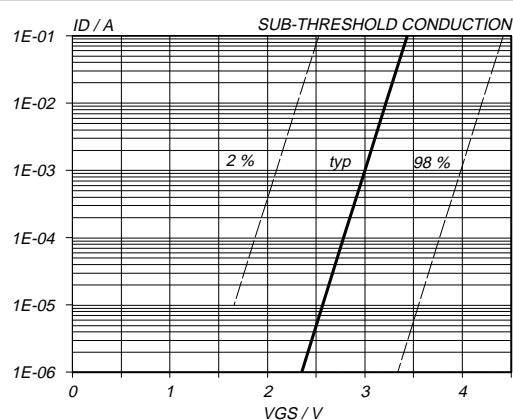


Fig.11. Sub-threshold drain current.
 $I_D = f(V_{GS})$; conditions: $T_j = 25^\circ\text{C}$; $V_{DS} = V_{GS}$

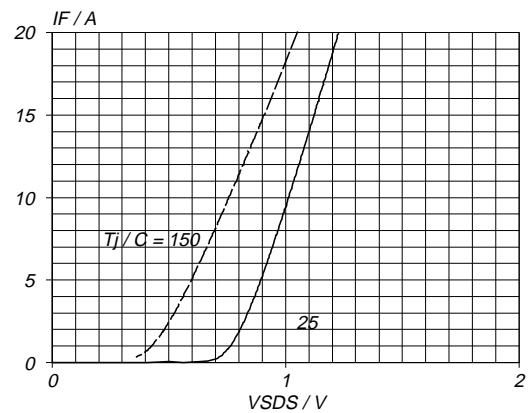


Fig.14. Typical reverse diode current.
 $I_F = f(V_{SDS})$; conditions: $V_{GS} = 0\text{ V}$; parameter T_j

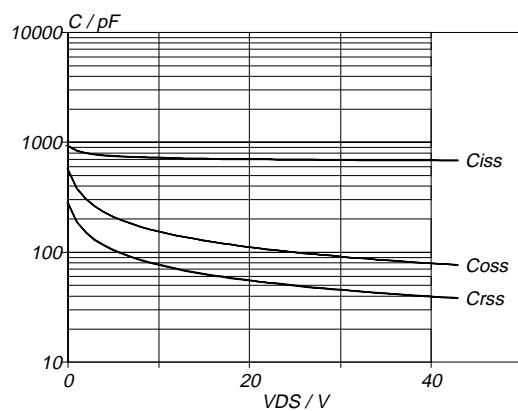


Fig.12. Typical capacitances, C_{iss} , C_{oss} , C_{rss} .
 $C = f(V_{DS})$; conditions: $V_{GS} = 0\text{ V}$; $f = 1\text{ MHz}$

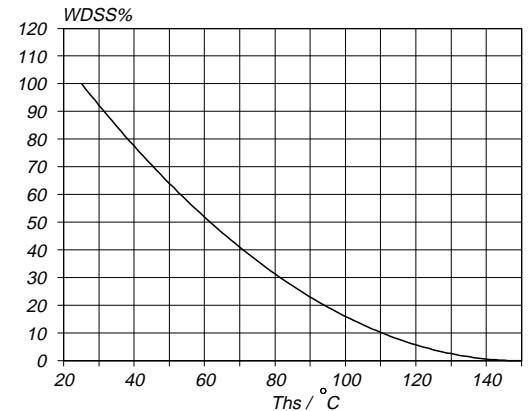


Fig.15. Normalised avalanche energy rating.
 $W_{DSS}\% = f(T_{hs})$; conditions: $I_D = 9\text{ A}$

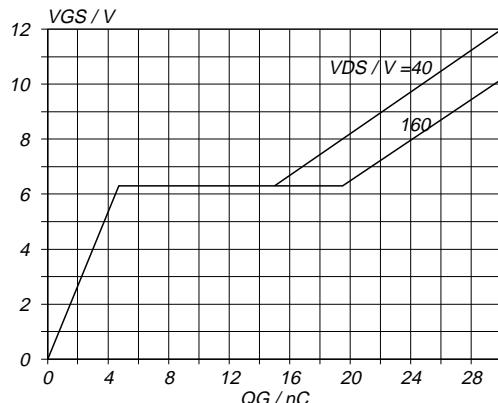


Fig.13. Typical turn-on gate-charge characteristics.
 $V_{GS} = f(Q_G)$; conditions: $I_D = 9\text{ A}$; parameter V_{DS}

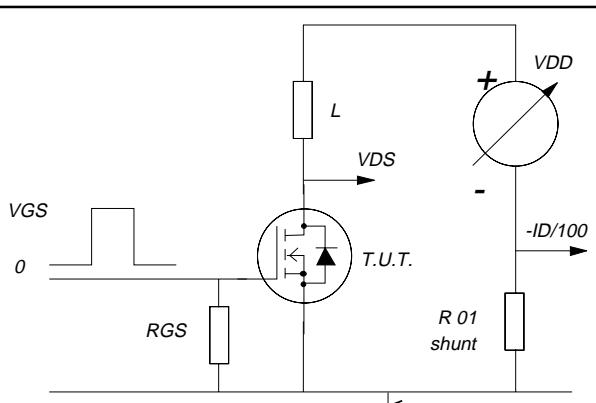


Fig.16. Avalanche energy test circuit.
 $W_{DSS} = 0.5 \cdot L I_D^2 \cdot BV_{DSS} / (BV_{DSS} - V_{DD})$

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MECHANICAL DATA

Dimensions in mm

Net Mass: 2 g

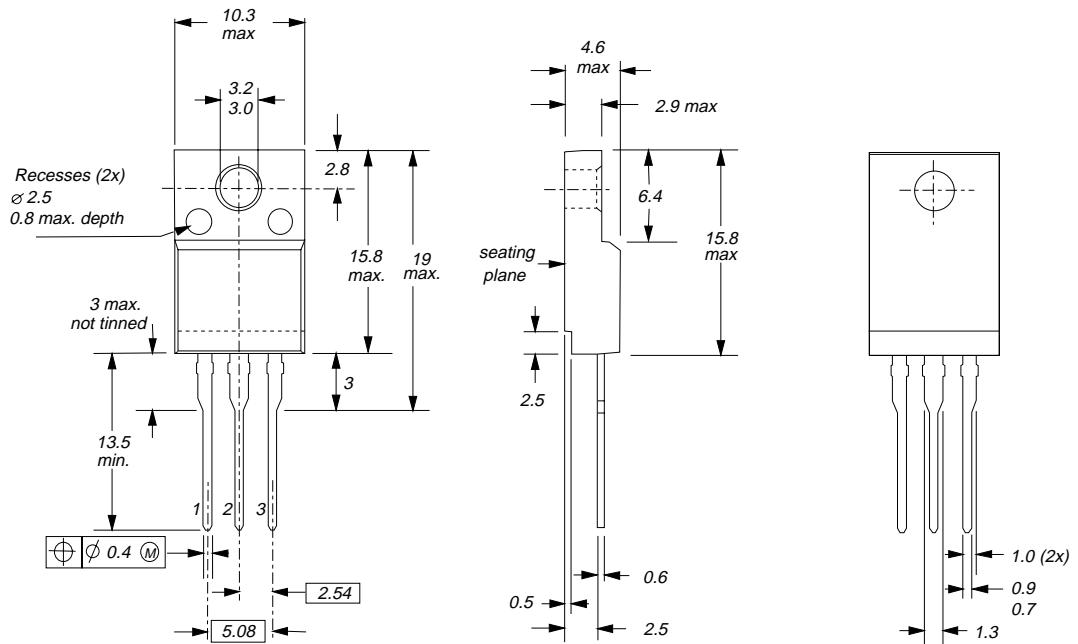


Fig. 17. SOT186A; The seating plane is electrically isolated from all terminals.

Notes

1. Observe the general handling precautions for electrostatic-discharge sensitive devices (ESDs) to prevent damage to MOS gate oxide.
2. Refer to mounting instructions for F-pack envelopes.
3. Epoxy meets UL94 V0 at 1/8".

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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	
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